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Lee et al.

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(54) **SEMICONDUCTOR LIGHT EMITTING DEVICE INCLUDING BONDING LAYER AND SEMICONDUCTOR LIGHT EMITTING DEVICE PACKAGE**

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(30) **Foreign Application Priority Data**

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(51) **Int. Cl.**
H01L 33/00 (2010.01)

(52) **U.S. Cl.** 257/99; 257/E33.063

(58) **Field of Classification Search** 257/96, 257/99, E33.063

See application file for complete search history.

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(57) **ABSTRACT**

A light emitting device is provided. The light emitting device comprises: a conductive support substrate; a bonding layer on the conductive support substrate; a reflective layer on the bonding layer; and a light emitting structure layer on the reflective layer. The bonding layer comprises a solder bonding layer on the conductive support substrate and at least one of a diffusion barrier layer and an adhesion layer on the solder bonding layer, the solder bonding layer, the diffusion barrier layer, and the adhesion layer being formed of a metal or an alloy of which the Young's Modulus is 9 GPa to 200 GPa.

19 Claims, 6 Drawing Sheets

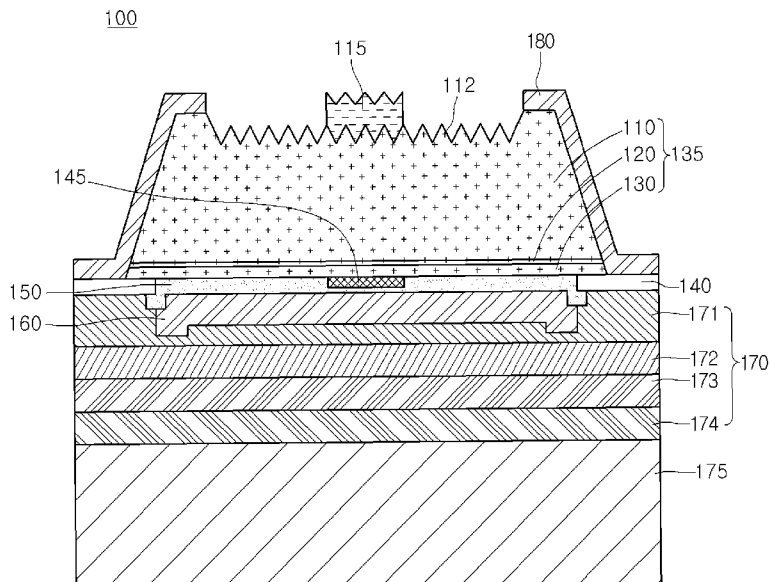


FIG. 1

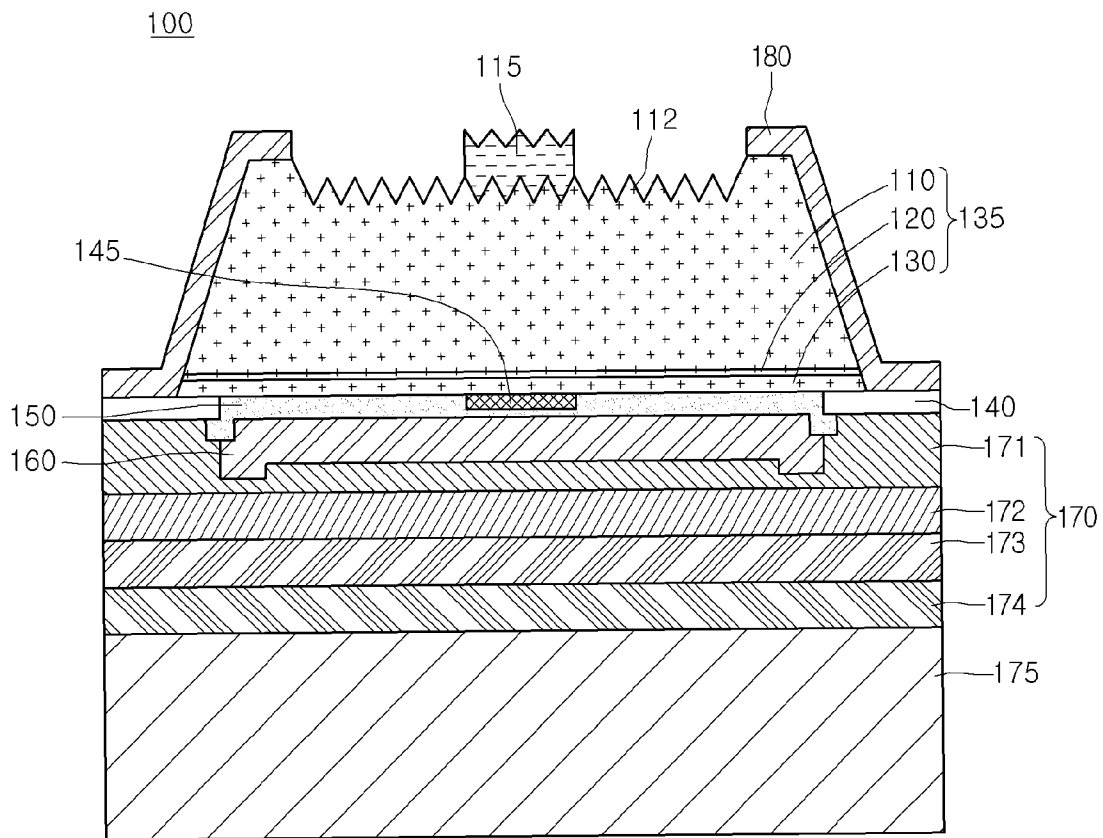


FIG. 2

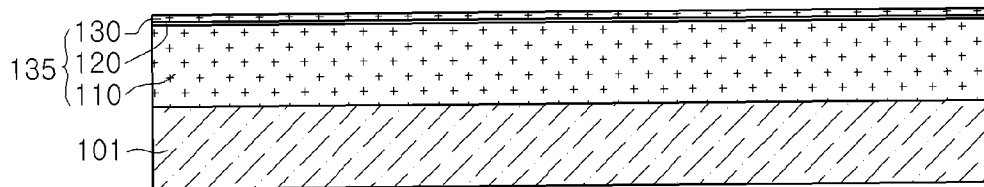


FIG. 3

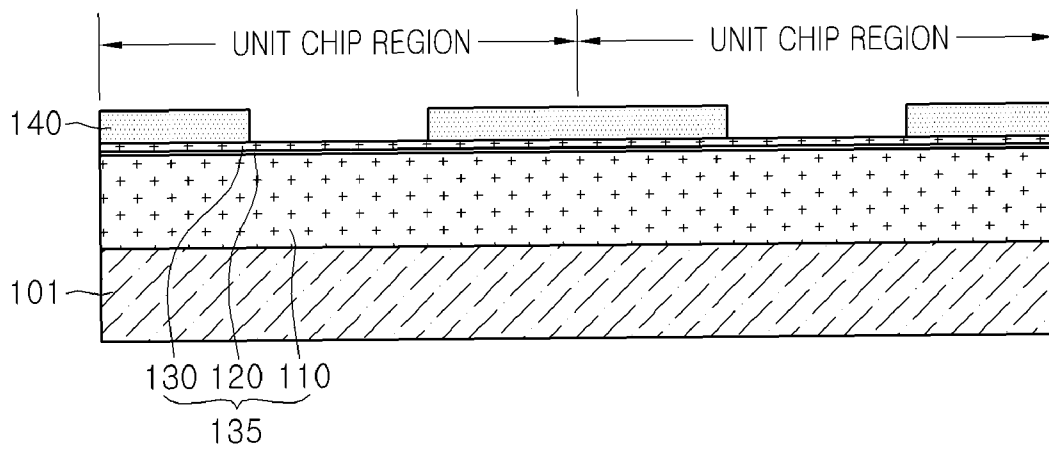


FIG. 4

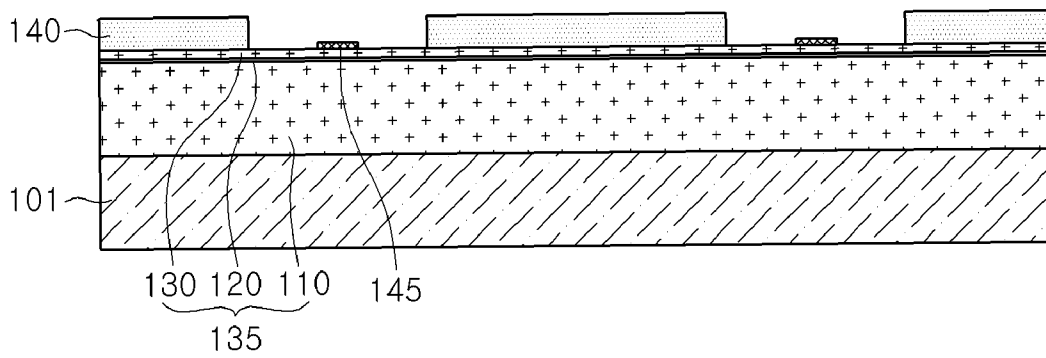


FIG. 5

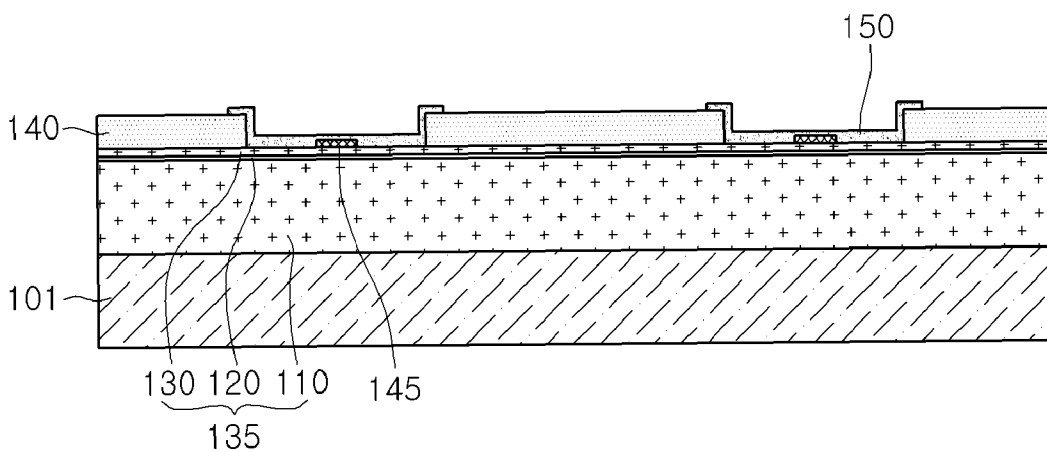


FIG. 6

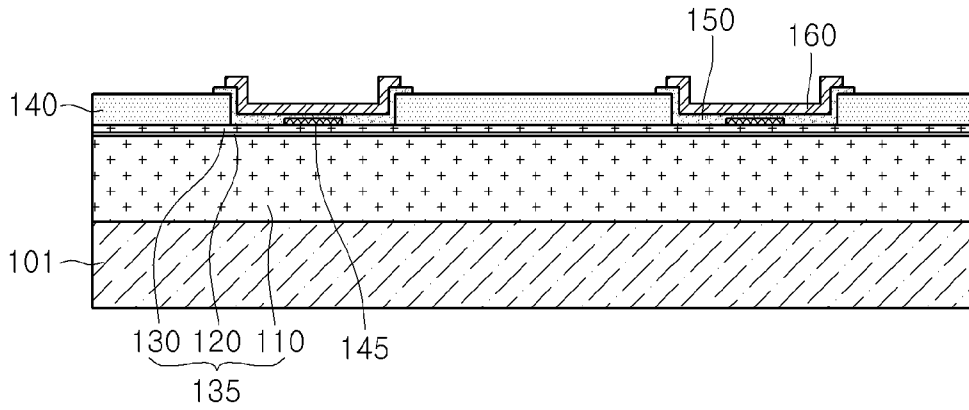


FIG. 7

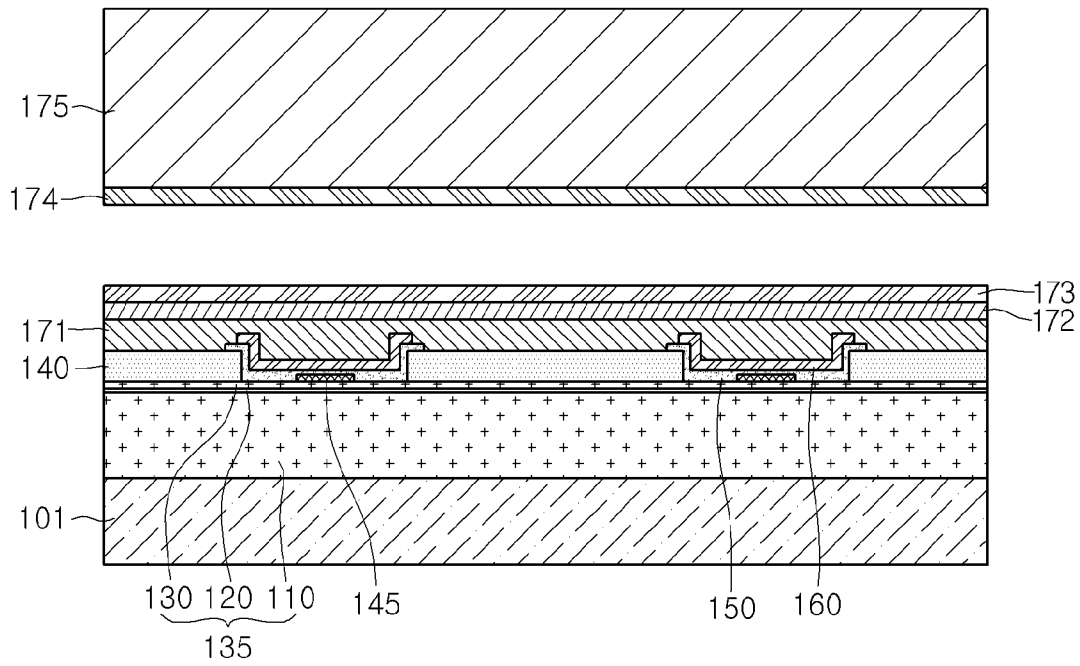


FIG. 8

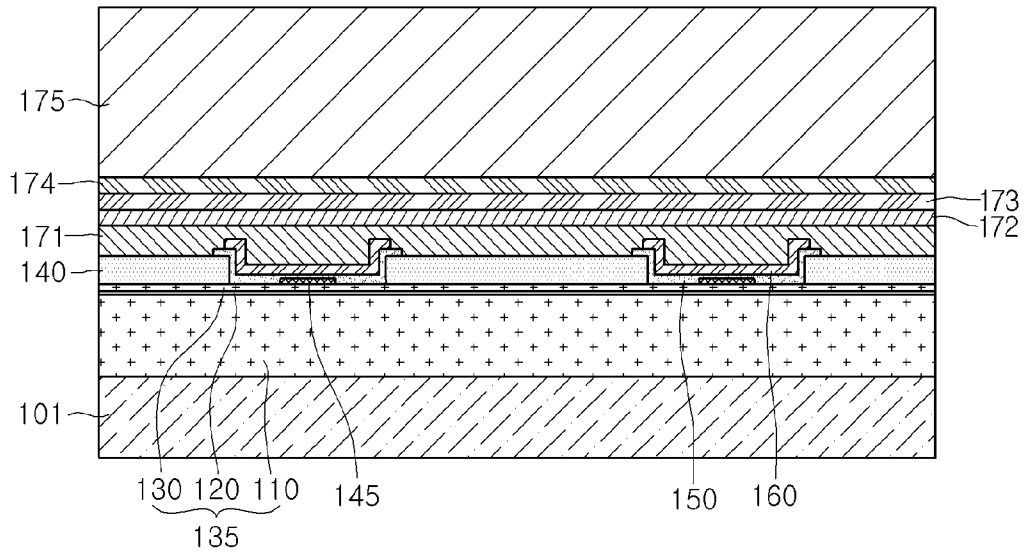


FIG. 9

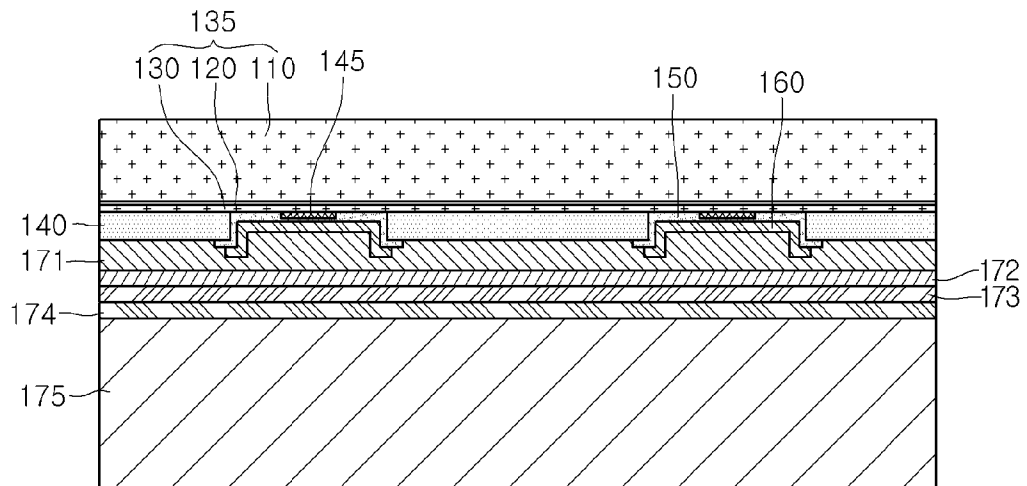


FIG. 10

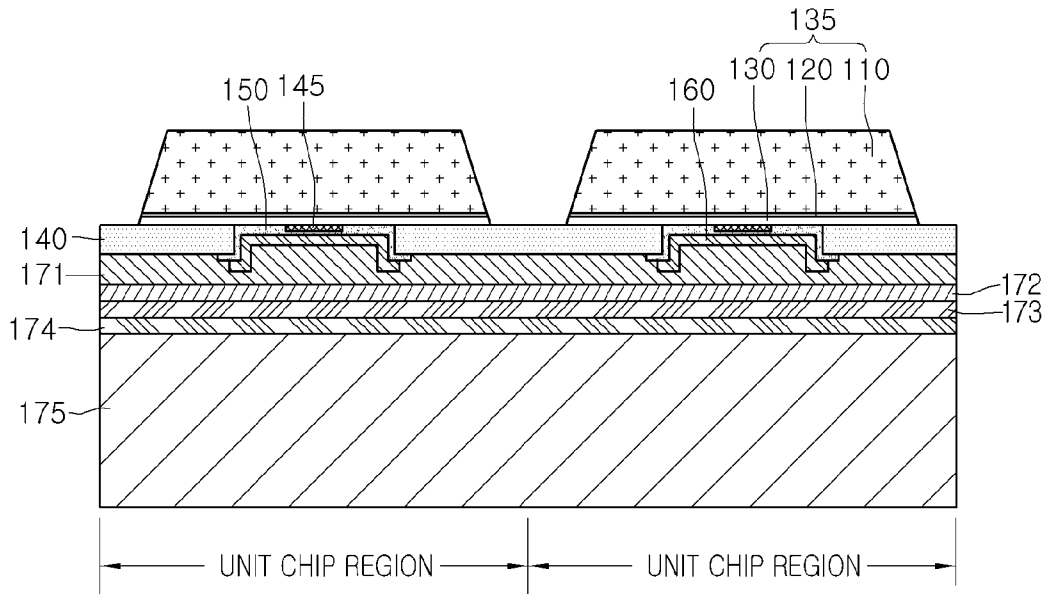


FIG. 11

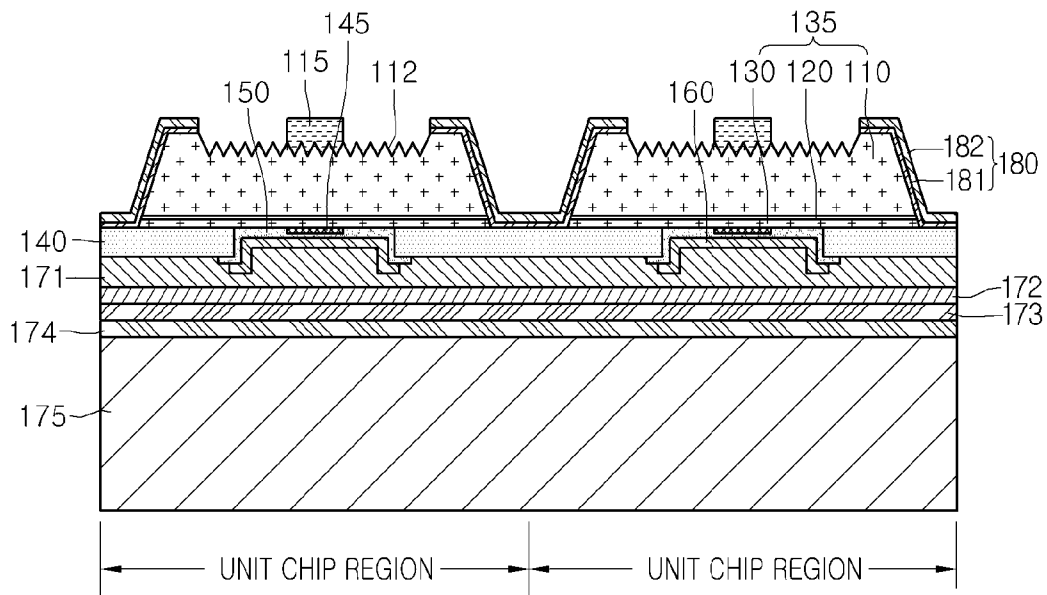
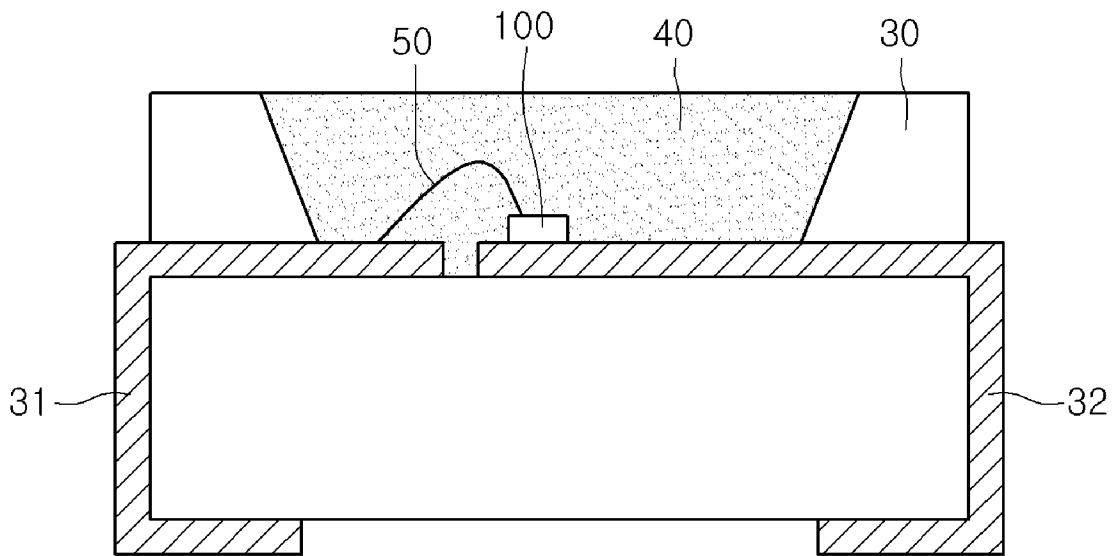


FIG. 12



**SEMICONDUCTOR LIGHT EMITTING
DEVICE INCLUDING BONDING LAYER AND
SEMICONDUCTOR LIGHT EMITTING
DEVICE PACKAGE**

CROSS-REFERENCE TO RELATED
APPLICATIONS

This application is a Continuation of application Ser. No. 12/702,674 filed on Feb. 9, 2010 now U.S. Pat. No. 7,928,464, which claims priority to Korean Patent Application No. 10-2009-0010703, filed on Feb. 10, 2009. The entire contents of all of the above applications are hereby incorporated by reference.

BACKGROUND

The present disclosure relates to a light emitting device and a light emitting device package.

A light emitting diode (LED) is a kind of a semiconductor device for converting electric energy into light. The LED has advantages such as low power consumption, a semi-permanent life cycle, a fast response time, safety, and environment friendly compared to the related art light source such as a fluorescent lamp and an incandescent bulb. Many studies are being in progress in order to replace the related art light source with an LED, and the LED is being increasingly used according to the trend as a light source of lighting equipment such as a variety of lamps, a liquid crystal display device, a scoreboard, a streetlight in indoor and outdoor places.

In the LED, a stacked light emitting structure layer includes a first conductive semiconductor layer, an active layer, and a second conductive semiconductor layer, and the light is generated from the light emitting structure layer according to an applied power supply.

In the LED, an epi-layer is used to form the light emitting structure layer on a growth substrate such as a sapphire substrate, and then a reflective layer is formed on the light emitting structure layer. Moreover, after bonding of the reflective layer and a conductive support substrate, an LED having a vertical structure is manufactured through a process for removing the growth substrate.

In addition, when the growth substrate is separated through a laser beam, due to a mechanical impact and explosive power of N₂ gas occurring during a thermo-chemical decomposition of a buffer layer material, crack or breaking occurs in the epi-layer.

Furthermore, in a case of Au—Sn, Au—In, Pd—In, Pd—Sn (i.e., a solder bonding material system) used for bonding the reflective layer and the conductive support substrate, materials such as Pt, W, and Cr are used as a diffusion barrier layer to prevent fast diffusion of Sn or In. At this point, in a case of Pt, a solder bonding material has an embrittlement property due to depletion of Sn or In and in a case of W and Cr, separation occurs due to a poor adhesiveness of Sn or In.

SUMMARY

The embodiments provide a light emitting device with a new structure.

The embodiments provide a light emitting device capable of preventing crack and breaking phenomenon occurring during the growth substrate separation.

The embodiments provide a light emitting device for preventing a solder bonding material from diffusing to a reflective layer or a light emitting structure layer

The embodiments provide a light emitting device for improving embrittlement and adhesiveness.

In an embodiment, a light emitting device comprises: a conductive support substrate; a bonding layer on the conductive support substrate; a reflective layer on the bonding layer; and a light emitting structure layer on the reflective layer, wherein the bonding layer comprises a solder bonding layer on the conductive support substrate and at least one of a diffusion barrier layer and an adhesion layer on the solder bonding layer, the solder bonding layer, the diffusion barrier layer, and the adhesion layer being formed of a metal or an alloy of which the Young's Modulus is 9 GPa to 200 GPa.

In another embodiment, a light emitting device comprises: a conductive support substrate; a solder bonding layer on the conductive support substrate; a diffusion barrier layer on the solder bonding layer; an adhesion layer on the diffusion barrier layer; a reflective layer on the adhesion layer; and a light emitting structure layer on the reflective layer, wherein the solder bonding layer, the diffusion barrier layer, and the adhesion layer are formed of a metal or an alloy; and the diffusion barrier layer or the adhesion layer is formed of a metal or an alloy including Cu or Nb.

In further another embodiment, a light emitting device package comprises: a package body; a first electrode and a second electrode installed on the package body; and a light emitting device connected to the first electrode and the second electrode electrically, wherein the light emitting device comprises: a conductive support substrate; a bonding layer on the conductive support substrate; a reflective layer on the bonding layer; and a light emitting structure layer on the reflective layer, wherein the bonding layer comprises a solder bonding layer on the conductive support substrate and at least one of a diffusion barrier layer and an adhesion layer on the solder bonding layer, the solder bonding layer, the diffusion barrier layer, and the adhesion layer being formed of a metal or an alloy of which the Young's Modulus is 9 GPa to 200 GPa.

The details of one or more embodiments are set forth in the accompanying drawings and the description below. Other features will be apparent from the description and drawings, and from the claims.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a view illustrating a light emitting device according to an embodiment.

FIGS. 2 to 11 are views illustrating a method of manufacturing a light emitting device according to an embodiment.

FIG. 12 is a sectional view of a light emitting device package including a light emitting device according to an embodiment.

DETAILED DESCRIPTION OF THE
EMBODIMENTS

In the descriptions of embodiments, it will be understood that when a layer (or film), a region, a pattern, or a structure is referred to as being 'on/above/over/upper' substrate, each layer (or film), a region, a pad, or patterns, it can be directly on substrate each layer (or film), the region, the pad, or the patterns, or intervening layers may also be present. Further, it will be understood that when a layer is referred to as being 'under/below/lower' each layer (film), the region, the pattern, or the structure, it can be directly under another layer (film), another region, another pad, or another patterns, or one or more intervening layers may also be present. Therefore, meaning thereof should be judged according to the spirit of the present disclosure.

In the figures, a dimension of each of elements may be exaggerated for clarity of illustration, and the dimension of each of the elements may be different from an actual dimension of each of the elements. Not all elements illustrated in the drawings must be included and limited to the present disclosure, but the elements except essential features of the present disclosure may be added or deleted.

Hereinafter, a light emitting device, a method of manufacturing the same, and a light emitting device package will be described below with reference to the accompanying drawings.

FIG. 1 is a view illustrating a light emitting device according to an embodiment.

Referring to FIG. 1, the light emitting device 100 includes a conductive support substrate 175, a bonding layer 170 on the conductive support substrate 175, a reflective layer 160 on the bonding layer 170, an ohmic contact layer 150 on the reflective layer 160, a protective layer 140 on a boundary region of the top of the bonding layer 170, a light emitting structure layer 135 on the ohmic contact layer 150 and the protective layer 140 to generate light, a passivation layer 180 for protecting the light emitting structure layer 135, a current blocking layer 145 between the reflective layer 160 and the light emitting structure layer 135, and an electrode unit 115 on the light emitting structure layer 135.

The conductive support substrate 175 supports the light emitting structure layer 135. The conductive support substrate 175 and the electrode unit 115 may apply a power to the light emitting structure layer 135. The conductive support substrate 175 includes at least one of Copper (Cu), Gold (Au), Nickel (Ni), Molybdenum (Mo), Copper-Tungsten (Cu—W), a carrier wafer (for example, Si, Ge, GaAs, ZnO, Sic, etc). The thickness of the conductive support substrate 175 may vary according to a design of the light emitting device 100, and may be 50 μm to 300 μm , for example.

The bonding layer 170 is formed on the conductive support substrate 175. The bonding layer 170 is formed below the reflective layer 160 and the protective layer 140. The bonding layer 170 contacts the reflective layer 160, the ohmic contact layer 150, and the protective layer 140 to allow them strongly to bond to the conductive support substrate 175.

The bonding layer 170 includes a solder bonding layer with a first solder bonding layer 173 and a second solder bonding layer 174, a diffusion barrier layer 172 on the first solder bonding layer 173, and an adhesion layer 171 on the diffusion barrier layer 172.

The bonding layer 170 prevents crack and breaking phenomenon occurring during a separation of a growth substrate, and also prevents a solder bonding material from being diffused into the reflective layer 160 or the light emitting structure layer 135. Also, the bonding layer 170 is formed to improve embrittlement and adhesiveness.

In the bonding layer 170, the adhesion layer 171 or the diffusion barrier layer 172 may be formed of a metal or an alloy of which the Young's Modulus is 9 GPa to 200 GPa and the first solder bonding layer 173 and the second solder bonding layer 174 may be formed of a material for a solder bonding alloy of which the Young's Modulus is 9 GPa to 200 GPa.

For example, the adhesion layer 171 may be formed with a thickness of 0.05 μm to 0.2 μm . The diffusion barrier layer 172 may be formed with a thickness of 1 μm to 3 μm . The solder bonding layer including the first solder bonding layer 173 and the second solder bonding layer 174 may be formed with a thickness of 2 μm to 4 μm .

For example, the adhesion layer 171 or the diffusion barrier layer 172 may be formed of a metal or an ally including at least one of Cu(129), Nb(105), Sn(49), In(10.1), Sc(79.3),

Ta(185.7), V(127.7), Si(113), Ag(82.7), Au(130), Zn(104.5), Sb(54.7), Al(70.6), Ge(79.9), Hf(141), La(37.9), Mg(44.7), Mn(191), Ni(199), Pd(121), and Ti(120). Moreover, for example, the first solder bonding layer 173 and the second solder bonding layer 174 may be formed of a metal or an alloy including at least one of Sn(49), In(10.5), Ga(9.8), Bi(34), Pb(16), and Au(130). However, the number in a parenthesis represents the Young's Modulus (GPa unit).

If materials used for the bonding layer 170 have the Young's Modulus of 9 GPa to 200 GPa, crack and breaking phenomenon occurring during the separation of the growth substrate can be prevented. Materials used for the adhesion layer 171 or the diffusion barrier layer 172 may prevent the diffusion of Sn or In of the first solder bonding layer 173 and the second solder bonding layer 174.

The adhesion layer 171 and the diffusion barrier layer 172 may be formed of the same material or respectively different materials. If the same material is used, only one of the adhesion layer 171 and the diffusion barrier layer 172 is formed.

In addition, the diffusion barrier layer 172 may be formed through an electro-plating or electroless-plating method besides physical vapor deposition (PVD) according to kinds of a selected material.

In this embodiment, the diffusion barrier layer 172 is formed of Cu or Nb, and has an excellent property for preventing crack and breaking phenomenon and diffusion of Sn or In.

For example, the adhesion layer 171/the diffusion barrier layer 172/the first and second solder bonding layers 173 and 174 may be formed of one of Ti—Ni/Cu/Au—Sn, Nb/Cu/Au—Sn, Nb/Nb—Sn/Au—In, or Nb/Nb/Au—Sn.

The reflective layer 160 may be formed on the bonding layer 170. The reflective layer 160 reflects light incident from the light emitting structure layer 135 such that light extraction efficiency can be improved. The reflective layer 160 may be selectively formed and may not be necessarily formed.

The reflective layer 160 may be formed of a metal or an alloy including at least one of Ag, Ni, Al, Rh, Pd, Ir, Ru, Mg, Zn, Pt, Au, and Hf. In addition, the reflective layer 160 may be formed with a multilayer using the above metal or alloy and a transparent conductive material such as IZO, IZTO, IAZO, IGZO, IGTO, AZO, and ATO. For example, the reflective layer 160 may be stacked by IZO/Ni, AZO/Ag, IZO/Ag/Ni, or AZO/Ag/Ni. For example, the reflective layer 160 may be formed of a metal or an alloy, which includes Ag.

In this embodiment, although it is illustrated that the top of the reflective layer 160 contacts the ohmic contact layer 150, the reflective layer 160 may contact the protective layer 140, the current blocking layer 145, or the light emitting structure layer 135.

The ohmic contact layer 150 may be formed on the reflective layer 160. The ohmic contact layer 150 ohmic-contacts the second conductive semiconductor layer 130 to smoothly provide a power to the light emitting structure layer 135 and may include at least one of ITO, IZO, IZTO, IAZO, IGZO, IGTO, AZO, and ATO. The ohmic contact layer 150 may be selectively formed and may not be necessarily formed.

That is, the ohmic contact layer 150 may selectively use a transparent conductive layer and a metal, and also may be realized with a single layer or a multilayer including at least one of indium tin oxide (ITO), indium zinc oxide (IZO), indium zinc tin oxide (IZTO), indium aluminum zinc oxide (IAZO), indium gallium zinc oxide (IGZO), indium gallium tin oxide (IGTO), aluminum zinc oxide (AZO), antimony tin oxide (ATO), gallium zinc oxide (GZO), IrOx, RuOx, RuOx/ITO, Ni, Ag, Ni/IrOx/Au, and Ni/IrOx/Au/ITO

In this embodiment, although it is illustrated that the ohmic contact layer **150** contacts the bottom and side of the current blocking layer **145**, the ohmic contact layer **150** may be disposed being spaced apart from the current blocking layer **145** or may contact only the side of the current blocking layer **145**. Moreover, the reflective layer **160** may be formed of a material that ohmic-contacts the second conductive semiconductor layer **130**, and the ohmic contact layer **150** may not be formed.

The current blocking layer **145** may be formed between the ohmic contact layer **150** and the second conductive semiconductor layer **130**. The current blocking layer **145** has the top that contracts the second conductive semiconductor layer **130** and also has the bottom and side that contact the ohmic contact layer **150**.

The current blocking layer **145** may be formed and its portion may vertically overlap the electrode unit **115**. Therefore, a phenomenon that current is concentrated on the shortest distance between the electrode unit **115** and the conductive support substrate **175** is alleviated to improve luminescence efficiency of the light emitting device **100**.

The current blocking layer **145** may be formed of a material having a lower electrical conductivity than the reflective layer **160** or the ohmic contact layer **150**, a material for Schottky contact with the second conductive semiconductor layer **130**, or an electrical insulation material, and may include at least one of ITO, IZO, IZTO, IAZO, IGZO, IGTO, AZO, ATO, ZnO, SiO₂, SiO_x, SiO_xN_y, Si₃N₄, Al₂O₃, TiO_x, Ti, Al, and Cr, for example.

The current blocking layer **145** may not be necessarily formed, and may be omitted according to a structure of the light emitting device **100**.

The protective layer **140** may be formed on a boundary region of the top of the bonding layer **170**. That is, the protective layer **140** may be formed on the boundary region between the light emitting structure layer **135** and the bonding layer **170**, and may be formed of a conductive protective layer using a conductive material or a non-conductive protective layer using a non-conductive material.

The conductive protective layer may be formed of a transparent conductive oxide layer or may include at least one of Ti, Ni, Pt, Pd, Rh, Ir, and W. For example, the transparent conductive oxide layer may be formed of at least one of indium tin oxide (ITO), indium zinc oxide (IZO), indium zinc tin oxide (IZTO), indium aluminum zinc oxide (IAZO), indium gallium zinc oxide (IGZO), indium gallium tin oxide (IGTO), aluminum zinc oxide (AZO), antimony tin oxide (ATO), and gallium zinc oxide (GZO).

In addition, if isolation etching is performed on the light emitting structure layer **135** to separate the light emitting structure layer **135** by a unit chip without the protective layer **140** during a chip separation process, fragments are generated from the bonding layer **170**. The fragments are attached between the second conductive semiconductor layer **130** and the active layer **120** or between the active layer **120** and the first conductive semiconductor layer **110**, such that electrical short may occur. Accordingly, the conductive protective layer is formed of a material that is not cracked or does not generate fragments during isolation etching. Therefore, the fragments of the bonding layer **170** are not generated and the electrical short is not occurred.

Since the conductive protective layer has electrical conductivity, current may be injected on the light emitting structure **135** through the conductive protective layer. Accordingly, light may effectively occur at the active layer **120** disposed on the conductive protective layer on a boundary

region of the light emitting structure layer **135** and also light efficiency of the light emitting device can be improved.

Moreover, the conductive protective layer reduces an operating voltage increased by the current blocking layer **145**, such that the operating voltage of the light emitting device can be lowered.

The conductive protective layer may be formed of the same material as the ohmic contact layer **150**.

The non-conductive protective layer has very low electrical conductivity and thus may be substantially formed of a non-conductive material. The non-conductive protective layer may be formed of a material having a considerably lower electrical conductivity than the reflective layer **160** or the ohmic contact layer **150**, a material for Schottky contact with the second conductive semiconductor layer **130**, or an electrical insulation material. For example, the non-conductive protective layer may be formed of ZnO or SiO₂.

The non-conductive protective layer increases the distance between the bonding layer **170** and the active layer **120**. Accordingly, probability that electrical short occurs between the bonding layer **170** and the active layer **120** can be reduced.

In addition, if isolation etching is performed on the light emitting structure layer **135** to separate the light emitting structure layer **135** by a unit chip without the non-protective layer **140** during a chip separation process, fragments are generated from the bonding layer **170**. The fragments are attached between the second conductive semiconductor layer **130** and the active layer **120** or between the active layer **120** and the first conductive semiconductor layer **110**, such that electrical short may occur.

The non-conductive protective layer is formed of a material that is not cracked or does not generate fragments during isolation etching or an electrical insulation material that does not cause electrical short even if its portion is cracked or a small amount of fragments are generated. Therefore, the fragments of the bonding layer **170** are not generated and the short circuit is not occurred.

The protective layer **140** partially overlaps the light emitting structure layer **135** in a vertical direction.

The protective layer **140** increases the distance of the side between the bonding layer **170** and the active layer **120**. Accordingly, probability that electrical short occurs between the bonding layer **170** and the active layer **120** can be reduced.

The protective layer **140** may not be necessarily formed, and may be omitted according to a structure of the light emitting device **100**.

The light emitting structure layer **135** may be formed on the ohmic contact layer **150** and the protective layer **140**.

An inclined plane may be formed at the side of the light emitting structure layer **135** while isolation etching is performed for the separation of a unit chip, and a portion of the inclined plane overlaps the protective layer **140** in a vertical direction.

A partial top of the protective layer **140** may be exposed by the isolation etching. Accordingly, the protective layer **140** contacts a partial region of the light emitting structure layer **135** in a vertical direction and the remaining portion does not contact the light emitting structure layer **135** in a vertical direction.

The light emitting structure layer **135** may include a compound semiconductor layer of a plurality of Group III to Group V elements, and may include a first conductive semiconductor layer **110**, an active layer **120** below the first conductive semiconductor layer **110**, and the second conductive semiconductor layer **130** below the active layer **120**.

The first conductive semiconductor layer **110** may be formed of a compound semiconductor of Group III to Group

V elements doped with a first conductive dopant, for example, GaN, AlN, AlGaIn, InGaIn, InN, InAlGaIn, AlInN, AlGaAs, GaP, GaAs, GaAsP, and AlGaInP. If the first conductive semiconductor layer **110** is an N-type semiconductor layer, the first conductive dopant includes an N-type dopant such as Si, Ge, Sn, Se, and Te. The first conductive semiconductor layer **110** may be formed with a single layer or a multilayer, but is not limited thereto.

The active layer **120** is formed below the first conductive semiconductor layer **110** and may include any one of a single quantum well structure, a multiple quantum well (MQW) structure, a quantum dot structure, and a quantum wire structure. The active layer **120** may be formed of a well layer and a barrier layer using a compound semiconductor material of Group III to Group V elements, such as InGaIn well layer/GaN barrier layer or InGaIn well layer/AlGaIn barrier layer.

A clad layer may be formed between the active layer **120** and the first conductive semiconductor layer **110** or between the active layer **120** and the second conductive semiconductor layer **130**. The clad layer may be formed of an AlGaIn based semiconductor.

The second conductive semiconductor layer **130** may be formed below the active layer **120** and is formed of a compound semiconductor of Group III to Group V elements doped with a second conductive dopant, for example, GaN, AlN, AlGaIn, InGaIn, InN, InAlGaIn, AlInN, AlGaAs, GaP, GaAs, GaAsP, and AlGaInP. If the second conductive semiconductor layer **130** is a P-type semiconductor layer, the second conductive dopant includes a P-type dopant such as Mg and Zn. The second conductive semiconductor layer **130** may be formed with a single layer or a multilayer, and is not limited thereto.

In addition, the light emitting structure layer **135** may include an N-type semiconductor layer below the second conductive semiconductor layer **130**. For example, the light emitting structure layer **135** may include at least one of N-P junction, P-N junction, N-P-N junction and P-N-P junction structures.

The electrode unit **115** is formed on the light emitting structure layer **135**. The electrode unit **115** may include a pad part for wire bonding and a finger part extending from the pad part. The finger part may be divided with a predetermined pattern and may be formed with various forms.

A roughness pattern **112** may be formed on the top of the first conductive semiconductor layer **110** to achieve light extraction efficiency. Accordingly, a roughness pattern may be formed on the electrode unit **115** and is not limited thereto.

The passivation layer **180** may be formed on at least the side of the light emitting structure layer **135**. Moreover, the passivation layer **180** may be formed on the first conductive semiconductor layer **110** and the protective layer **140**, but is not limited thereto.

The passivation layer **180** may be formed to electrically protect the light emitting structure layer **135**.

For example, the passivation layer **180** may be formed of at least one of oxide silicon (SiO_x), oxide nitride silicon (SiO_xN_y), nitride silicon (Si_3N_4), and oxide aluminum (Al_2O_3).

Hereinafter, a method of manufacturing a light emitting device will be described in more detail according to an embodiment. However, the overlapping description will be omitted or briefly described again.

FIGS. 2 to 11 are views illustrating a method of manufacturing a light emitting device according to an embodiment.

Referring to FIG. 2, a light emitting structure layer **135** is formed on a growth substrate **101**. The growth substrate **101**

may be formed of at least one of sapphire (Al_2O_3), SiC, GaAs, GaN, ZnO, Si, GaP, InP, and Ge, and is not limited thereto.

The light emitting structure layer **135** may be formed by growing a first conductive semiconductor layer **110**, an active layer **120**, and a second conductive semiconductor layer **130** on the growth substrate **101**.

The light emitting structure layer **135** may be formed through various methods such as Metal Organic Chemical Vapor Deposition (MOCVD), Chemical Vapor Deposition (CVD), Plasma-Enhanced Chemical Vapor Deposition (PECVD), Molecular Beam Epitaxy (MBE), and Hydride Vapor Phase Epitaxy (HVPE), and is not limited thereto.

In addition, a buffer layer (not shown) and/or an undoped nitride layer (not shown) may be formed between the light emitting structure layer **135** and the growth substrate **101** in order to alleviate a lattice mismatch due to a lattice constant difference.

Referring to FIG. 3, a protective layer **140** is selectively formed on the light emitting structure layer **135**, being corresponding to a unit chip region.

The protective layer **140** may be formed on a boundary of the unit chip region using a mask pattern. The protective layer **140** may be formed using various deposition methods such as a sputtering method.

Referring to FIG. 4, a current blocking layer **145** may be formed on the second conductive semiconductor layer **130**. The current blocking layer **145** may be formed using a mask pattern.

The protective layer **140** and the current blocking layer **145** may be formed of the same material. In this case, the protective layer **140** and the current blocking layer **145** may be simultaneously formed using one process without an additional process. For example, after a SiO_2 layer is formed on the second conductive semiconductor layer **130**, the protective layer **140** and the current blocking layer **145** may be simultaneously formed using a mask pattern.

Referring to FIGS. 5 and 6, an ohmic contact layer **150** is formed on the second conductive semiconductor layer **130** and the current blocking layer **145**, and then a reflective layer **160** may be formed on the ohmic contact layer **150**.

The ohmic contact layer **150** and the reflective layer **160** may be formed using one of E-beam deposition, Sputtering, and Plasma Enhanced Chemical Vapor Deposition (PECVD).

Referring to FIGS. 7 and 8, a conductive support substrate **175** is prepared.

An adhesion layer **171**, a diffusion barrier layer **172**, and a first solder bonding layer **173** are formed on the protective layer **140** and the reflective layer **160**, and then a second solder bonding layer **174** is formed on the conductive support substrate **175**. For example, the adhesion layer **171**, the first solder bonding layer **173**, and the second solder bonding layer **174** are formed using a PVD method, and the diffusion barrier layer **172** may be formed using an electro-plating or electroless-plating method besides the PVD method.

Furthermore, since the first solder bonding layer **173** is attached to the second solder bonding layer **174**, the structure of FIG. 6 is attached to the conductive support substrate **175** by a bonding layer **170**.

Referring to FIG. 9, the growth substrate **101** is removed from the light emitting structure layer **135**. FIG. 9 is a reversed view of the structure of FIG. 8.

The growth substrate **101** may be removed by a Laser Lift Off method or a Chemical Lift Off method.

Since materials used for the bonding layer **170** have the Young's Modulus of 9 GPa to 200 GP, crack and breaking phenomenon occurring during the separation of the growth substrate **101** can be prevented.

Referring to FIG. 10, isolation etching is performed on the light emitting structure layer 135 by a unit chip region, such that a plurality of light emitting structure layers 135 are divided. For example, the isolation etching may be performed using a dry etching method such as Inductively Coupled Plasma (ICP).

Referring to FIG. 11, a passivation layer 180 is formed on the protective layer 140 and the light emitting structure layer 135, and then is selectively removed to expose the top of the first conductive semiconductor layer 110.

Then, a roughness pattern 112 is formed on the first conductive semiconductor layer 110 to improve light extraction efficiency, and an electrode part 115 is formed on the roughness pattern 112. The roughness pattern 112 may be formed through a wet etching process or a dry etching process.

Then, the structure is separated by a unit chip region through a chip separation process such that a plurality of light emitting devices can be manufactured.

The chip separation process may include a breaking process for separating a chip by applying a physical impact using a blade, a laser scribing process for separating a chip by projecting laser on a chip boundary, and an etching process including wet or dry etching, but is not limited thereto.

FIG. 12 is a sectional view of a light emitting device package including a light emitting device according to an embodiment.

Referring to FIG. 12, the light emitting device package includes a package body 30, a first electrode 31 and a second electrode 32 installed at the package body 30, a light emitting device 100 installed at the package body 30 to electrically connect to the first electrode 31 and the second electrode 32, and a molding member 40 surrounding the light emitting device 100.

The package body 30 may be formed including a silicon material, a synthetic resin material, or a metal material, and may have a cavity whose side is inclined.

The first electrode 31 and the second electrode 32 are electrically separated from each other and provide a power to the light emitting device 100. In addition, the first electrode 31 and the second electrode 32 reflects a light generated from the light emitting device 100 to increase light efficiency, and exhausts a heat generated from the light emitting device 100 to the external.

The light emitting device 100 is installed on the package body 30, the first electrode 31, or the second electrode 32.

The light emitting device 100 may be electrically connected to one of the first electrode 31 and the second electrode 32 using one of a wire method, a flip chip method, or a die bonding method. In this embodiment, it is illustrated that the light emitting device 100 is electrically connected to the first electrode 31 through a wire 50 and directly electrically contacts the second electrode 32.

The molding member 40 surrounds the light emitting device 100 such that the light emitting device 100 can be protected. In addition, the molding member 40 includes a fluorescent substance such that a wavelength of a light emitted from the light emitting device 100 can be changed.

The embodiments can provide a light emitting device with a new structure.

The embodiments can provide a light emitting device capable of preventing crack and breaking phenomenon occurring during the growth substrate separation.

The embodiments can provide a light emitting device for preventing a solder bonding material from diffusing to a reflective layer or a light emitting structure layer

The embodiments can provide a light emitting device for improving embrittlement and adhesiveness.

Any reference in this specification to “one embodiment,” “an embodiment,” “example embodiment,” etc., means that a particular feature, structure, or characteristic described in connection with the embodiment is included in at least one embodiment of the invention. The appearances of such phrases in various places in the specification are not necessarily all referring to the same embodiment. Further, when a particular feature, structure, or characteristic is described in connection with any embodiment, it is submitted that it is within the purview of one skilled in the art to effect such feature, structure, or characteristic in connection with other ones of the embodiments.

Although embodiments have been described with reference to a number of illustrative embodiments thereof, it should be understood that numerous other modifications and embodiments can be devised by those skilled in the art that will fall within the spirit and scope of the principles of this disclosure. More particularly, various variations and modifications are possible in the component parts and/or arrangements of the subject combination arrangement within the scope of the disclosure, the drawings and the appended claims. In addition to variations and modifications in the component parts and/or arrangements, alternative uses will also be apparent to those skilled in the art.

What is claimed is:

1. A semiconductor light emitting device comprising:
a bonding layer;

a barrier layer on the bonding layer;

an adhesion layer on the barrier layer;

a reflective layer on the adhesion layer;

a light emitting structure layer on the reflective layer; and
a passivation layer comprising an insulating material on a side surface and a top surface of the light emitting structure layer,

wherein the light emitting structure layer comprises a first conductive semiconductor layer, a second conductive semiconductor layer, and an active layer between the first conductive semiconductor layer and the second conductive semiconductor layer,

wherein the second conductive semiconductor layer is closer to the reflective layer than the first conductive semiconductor layer,

wherein a top surface area of the second conductive semiconductor layer is greater than a top surface area of the first conductive semiconductor layer,

wherein a bottom surface of the barrier layer covers all of a top surface of the bonding layer,

wherein the bonding layer comprises Au—Sn,

wherein the barrier layer comprises at least one of Cu or Ti,

wherein the reflective layer comprises Ni—Ag, and

wherein the adhesion layer comprises Au—Sn.

2. The semiconductor light emitting device according to claim 1, further comprising an electrode on the light emitting structure layer.

3. The semiconductor light emitting device according to claim 1, further comprising an ohmic contact layer between the reflective layer and the light emitting structure layer.

4. The semiconductor light emitting device according to claim 1, further comprising a current blocking layer between the reflective layer and the light emitting structure layer.

5. The semiconductor light emitting device according to claim 1, further comprising a protective layer on the adhesion layer.

6. The semiconductor light emitting device according to claim 1, wherein the first conductive semiconductor layer comprises a roughness pattern.

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7. A semiconductor light emitting device comprising:
 a first adhesion layer;
 a first barrier layer on the first adhesion layer;
 a second barrier layer on the first barrier layer;
 a second adhesion layer on the barrier layer;
 a reflective layer on the second adhesion layer;
 a light emitting structure layer on the reflective layer; and
 a passivation layer comprising an insulating material on a
 side surface and a top surface of the light emitting structure
 layer,
 wherein the light emitting structure layer comprises a first
 conductive semiconductor layer, a second conductive
 semiconductor layer, and an active layer between the
 first conductive semiconductor layer and the second
 conductive semiconductor layer,
 wherein the second conductive semiconductor layer is
 closer to the reflective layer than the first conductive
 semiconductor layer,
 wherein a top surface area of the second conductive semi-
 conductor layer is greater than a top surface area of the
 first conductive semiconductor layer,
 wherein a bottom surface of the first barrier layer covers all
 of a top surface of the first adhesion layer, wherein the
 first adhesion layer, the first barrier layer, the second
 barrier layer and the second adhesion layer being formed
 of a metal or an alloy of which the Young's Modulus is 9
 GPa to 200 GPa,
 wherein the first barrier layer comprises a metal or an alloy
 including at least one of Cu or Si, and
 wherein the second barrier layer comprises Ti.

8. The semiconductor light emitting device according to
 claim 7,
 wherein the first adhesion layer comprises Au—Sn, and
 wherein the second adhesion layer comprises a metal or an
 alloy including at least one of Ni or Ti.

9. The semiconductor light emitting device according to
 claim 7,
 wherein the first adhesion layer comprises Au—Sn, and
 wherein the second adhesion layer comprises a metal or an
 alloy including Au, Pd and Sn.

10. The semiconductor light emitting device according to
 claim 7,
 wherein the first adhesion layer comprises Au—Sn, and
 wherein the second adhesion layer comprises a metal or an
 alloy including Au, Ni and Sn.

11. The semiconductor light emitting device according to
 claim 7, further comprising an electrode on the light emitting
 structure layer.

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12. The semiconductor light emitting device according to
 claim 7, further comprising a current blocking layer between
 the reflective layer and the light emitting structure layer.

13. The semiconductor light emitting device according to
 claim 7, further comprising a protective layer on the second
 adhesion layer.

14. A semiconductor light emitting device comprising:
 a bonding layer;
 a barrier layer on the bonding layer;
 an adhesion layer on the barrier layer;
 a reflective layer on the adhesion layer;
 a light emitting structure layer on the reflective layer; and
 a passivation layer comprising an insulating material on a
 side surface and a top surface of the light emitting structure
 layer,

wherein the light emitting structure layer comprises a first
 conductive semiconductor layer, a second conductive
 semiconductor layer, and an active layer between the
 first conductive semiconductor layer and the second
 conductive semiconductor layer,

wherein the second conductive semiconductor layer is
 closer to the reflective layer than the first conductive
 semiconductor layer,

wherein a top surface area of the second conductive semi-
 conductor layer is greater than a top surface area of the
 first conductive semiconductor layer,

wherein a bottom surface of the barrier layer covers all of
 a top surface of the bonding layer,

wherein the bonding layer comprises Au—Sn,
 wherein the barrier layer comprises at least one of Cu or Ti,
 wherein the reflective layer comprises Ni—Ag, and
 wherein the adhesion layer comprises Pd—Sn.

15. The semiconductor light emitting device according to
 claim 14, further comprising an electrode on the light emit-
 ting structure layer.

16. The semiconductor light emitting device according to
 claim 14, further comprising an ohmic contact layer between
 the reflective layer and the light emitting structure layer.

17. The semiconductor light emitting device according to
 claim 14, further comprising a current blocking layer between
 the reflective layer and the light emitting structure layer.

18. The semiconductor light emitting device according to
 claim 14, further comprising a protective layer on the adhe-
 sion layer.

19. The semiconductor light emitting device according to
 claim 14, wherein the first conductive semiconductor layer
 comprises a roughness pattern.

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